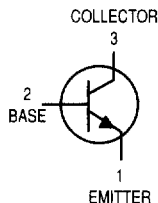


High Voltage Transistors

NPN Silicon



MPSA42*

MPSA43

*Motorola Preferred Device



CASE 29-04, STYLE 1
TO-18 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	MPSA42	MPSA43	Unit
Collector-Emitter Voltage	V_{CEO}	300	200	Vdc
Collector-Base Voltage	V_{CBO}	300	200	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	6.0	Vdc
Collector Current — Continuous	I_C	500		mA dc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625	5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5	12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{mW}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{mW}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0 \text{ mA dc}, I_B = 0$)	MPSA42 MPSA43	$V_{(BR)CEO}$	300 200	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100 \mu\text{A dc}, I_E = 0$)	MPSA42 MPSA43	$V_{(BR)CBO}$	300 200	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \mu\text{A dc}, I_C = 0$)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 200 \text{ Vdc}, I_E = 0$) ($V_{CB} = 160 \text{ Vdc}, I_E = 0$)	MPSA42 MPSA43	I_{CBO}	— —	0.1 0.1	$\mu\text{A dc}$
Emitter Cutoff Current ($V_{EB} = 6.0 \text{ Vdc}, I_C = 0$) ($V_{EB} = 4.0 \text{ Vdc}, I_C = 0$)	MPSA42 MPSA43	I_{EBO}	— —	0.1 0.1	$\mu\text{A dc}$

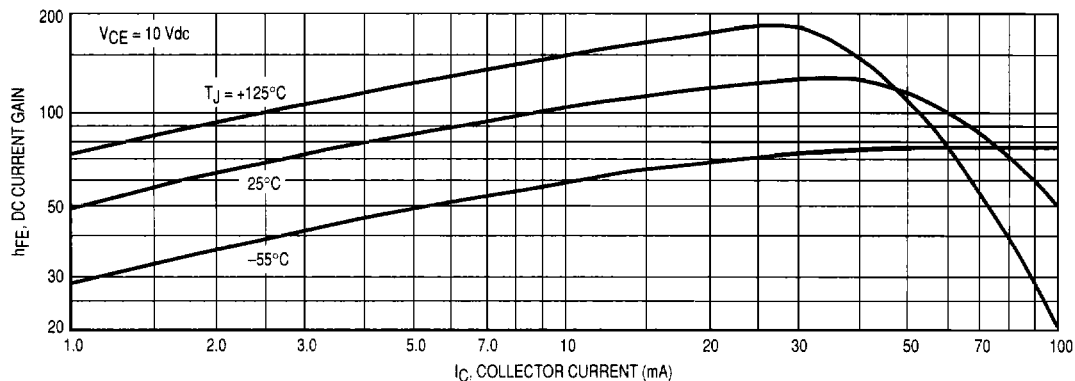
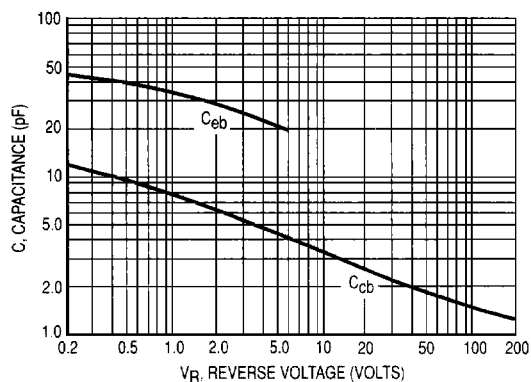
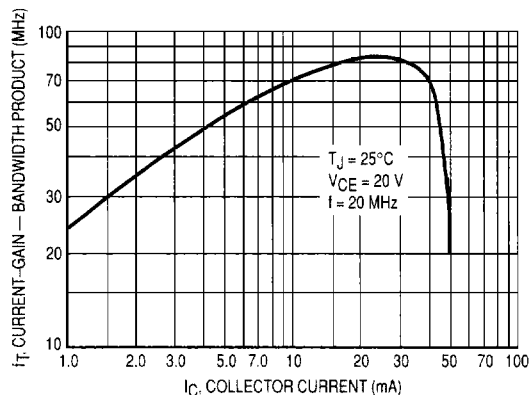
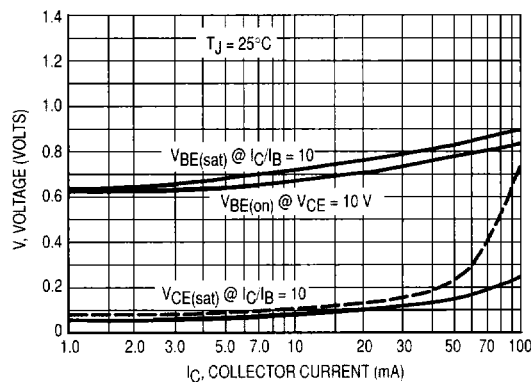
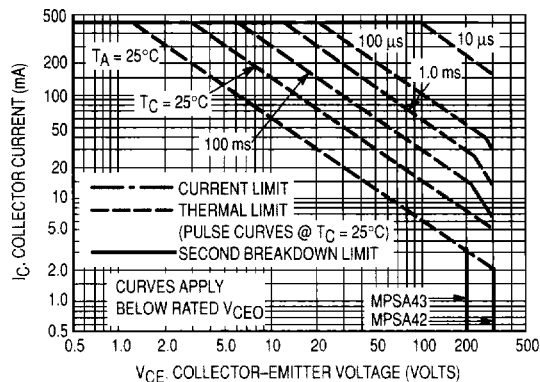
1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Preferred devices are Motorola recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 30\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	25 40 40	— — —	—
Collector–Emitter Saturation Voltage ($I_C = 20\text{ mAdc}$, $I_B = 2.0\text{ mAdc}$)	$V_{CE(sat)}$	— —	0.5 0.4	Vdc
Base–Emitter Saturation Voltage ($I_C = 20\text{ mAdc}$, $I_B = 2.0\text{ mAdc}$)	$V_{BE(sat)}$	—	0.9	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product ($I_C = 10\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	50	—	MHz
Collector–Base Capacitance ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{cb}	— —	3.0 4.0	pF

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.


Figure 1. DC Current Gain

Figure 2. Capacitances

Figure 3. Current-Gain — Bandwidth Product

Figure 4. "On" Voltages

Figure 5. Maximum Forward Bias Safe Operating Area